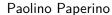
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Thèse n. 1234 2020 présentée le 18 novembre 2020 à la Faculté des sciences de base laboratoire SuperScience programme doctoral en SuperScience École polytechnique fédérale de Lausanne

pour l'obtention du grade de Docteur ès Sciences par



acceptée sur proposition du jury :

Prof Name Surname, président du jury Prof Name Surname, directeur de thèse Prof Name Surname, rapporteur Prof Name Surname, rapporteur Prof Name Surname, rapporteur

Lausanne, EPFL, 2020



Wings are a constraint that makes it possible to fly.

— Robert Bringhurst

To my parents...

Preface

A preface is not mandatory. It would typically be written by some other person (eg your thesis director).

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Lausanne, 12 Mars 2011

T. D.

Abstract

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Zusammenfassung

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Résumé

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1 Introduction

1.1 AlScN as the material of the future

Since the beginning of the decade Aluminum-Scandium Nitride became more and more a common buzzword in scientific publications. The main reasons behind the increased interest on this novel materials are two: IC fabrication compatibility and most importantly increased piezoelectric coupling.

1.2 Material properties

The first occurrency of an alloying of aluminum and scandium was in 1971 (1) and its first application was to improve the strain resistance of Al in aeronautics application. With the advent of miniaturisation in FR front-ends the bulky Quartz crystal started to be replace by MEMS-based resonator such as SAW, BAW, or CMR. The reason being that MEMS devices have a higher throughput and a lower footprint than quartz crystals, allowing for batch fabrication and integrability, still keeping the higher Q that mechanical systems show compared to LC tanks. In parallel to the architecture evolution of RF MEMS a range of new materials to replace quartz have been investigated, PZT, ZnO, AlN. The latter is the most important one to understand how the evolution of AlScN.

1.2.1 AlN

Aluminum Nitride is a binary nitride ceramic whose wirtzite phase exhibits piezoelectric properties. AlN can be deposited on a proper seed layer so that the growth is oriented in the c-axis (the perpendicular to surface axis) in a wurtzite phase. The crystal phase depends on the seed layer over which AlN is deposited. Literature (2) shows that the preferential growth substrate material for AlN is Pt, due to the lattice amtching between the Hexagonal structure of AlN and the cubic phase of Pt.

1.3 Deposition of AlScN

Piezoelectricity in AlN is a consequence of the dipolar nature of the crystalline cell of wurtzite-type crystal. From the first studies using DFT (1) (3) show that the doping of aluminum with scandium increases the piezoelectric coupling coefficient of AlN. The reason lies in the lattice distortion induced by Sc in Aln, causing a structural phase transition. According to (3) a second effect on the piezoelectricity improvement lies in the hybridisation of ionic into covalent bond, due to the lower electronegativity of Sc compared to Al (1.36 vs 1.61). An increase of the concentration of Sc results in an enhancement of response up to 43% Sc followed by a drastic performance drop. The actual state-of art includes depositions carried with Sputtering (4) (5) (6), co-sputtering (3), Molecular Beam Epitaxy (7) (8) (?), Metal-Organic CVD (9)

1.3.1 Sputtering of AlScN

The first and most simple to describe method for AlScN deposition is sputtering from an alloyed target using reactive sputtering.

- 1.3.2 Co-Sputtering of AlScN
- 1.3.3 MBE of AlScN
- 1.3.4 MOCVD of AlScN

1.4 Types of MEMS Resonator

Body 1 Part I

2 State of research

In this chapter we will see some examples of tables and figures.

2.1 Fabrication of AlScN based Contour Mode resonators

2.1.1 Sputtering deposition optimisaton

Carried over from the doctoral studies of Kaitlin M. Howell (10) the first objective of research in AlScN technologies is to optimize the deposition of AlScN in the Spider600 cluster tool at CMi. The Spider600 is a sputtering cluster which allows deposition from different targets in the same fabrication round, without breaking the vacuum

AlScN on AlN

2.1.2 Inductively coupled plasma etching

2.1.3 CMR based oscillator

Let's see how to make a well designed table.

The table 2.1 is a floating table and was obtained with the following code:

1 \begin{table}[tb]

Table 2.1: A floating table.

name	weight	food
mouse	10 g	cheese
cat	1 kg	mice
dog	10 kg	cats
t-rex	10 Mg	dogs

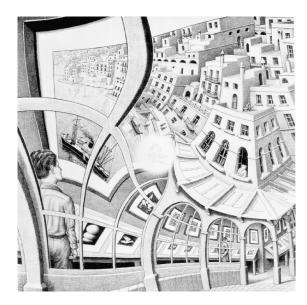


Figure 2.1: A floating figure (the lithograph *Galleria di stampe*, of M. Escher, got from http://www.mcescher.com/).

```
2 \caption[A floating table]{A floating table.}
3 \label{tab:example}
4 \centering
5
  \begin{tabular}{ccc}
  \toprule
              & weight & food
      name
8 \midrule
              & 10 g & cheese \\
              & 1 kg & mice
10
       cat
                                11
      dog
              & 10 kg & cats
                                \\
11
             & 10 Mg & dogs
      t-rex
12
13
  \bottomrule
14 \end{tabular}
15 \end{table}
```

2.2 Figures

Let's see now how to put one or several images in your text.

The figure 2.1 is a floating figure and was obtained with the following code:

```
1 \begin{figure}[tb]
2 \centering
3 \includegraphics[width=0.5\columnwidth]{galleria_stampe}
4 \caption[A floating figure]{A floating figure ... }
5 \label{fig:galleria}
6 \end{figure}
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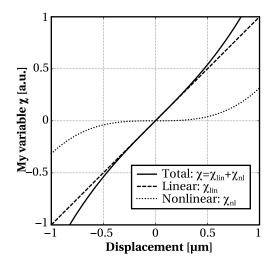


Figure 2.2: A floating figure with text typeset in "Utopia Latex", a font provided in the templatefolder for typesetting figures with greek characters. The text has been "outlined" for best compatibility with the repro during the printing.

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The figure 2.3 is a floating figure and was obtained with the following code:

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1 \begin{figure}[tb]
2 \centering
3 \subfloat[Asia personas duo.]
4 {\includegraphics[width=.45\columnwidth]{lorem}} \quad
5 \subfloat[Pan ma signo.]
6 {\label{fig:ipsum}%
7 \includegraphics[width=.45\columnwidth]{ipsum}} \\
8 \subfloat[Methodicamente o uno.]
9 {\includegraphics[width=.45\columnwidth]{dolor}} \quad
10 \subfloat[Titulo debitas.]
11 {\includegraphics[width=.45\columnwidth]{sit}}
12 \caption[Tu duo titulo debitas latente]{Tu duo titulo debitas latente.}
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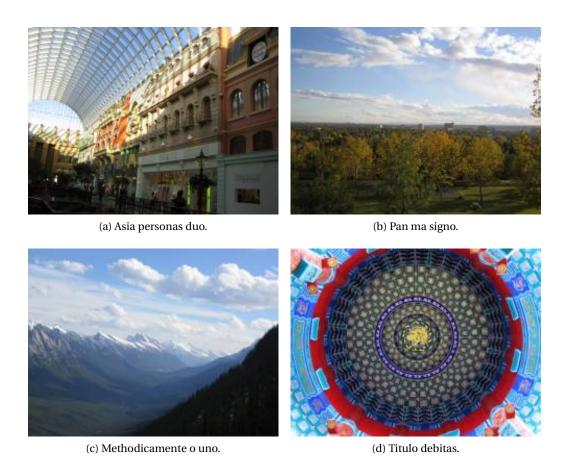


Figure 2.3: Tu duo titulo debitas latente.

13 \label{fig:esempio}
14 \end{figure}

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Body 2 Part II

3 Future research

In this chapter we will see some examples of mathematics.

3.1 N77 N78 and N79 band

3.1.1 Stepper-based fabrication of electrodes

3.2 AlScN on SiC power

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$$\frac{\mathrm{d}}{\mathrm{d}t} \begin{bmatrix} P_0 \\ P_I \\ P_T \end{bmatrix} = \begin{bmatrix} \frac{P_1}{\tau_{10}} + \frac{P_T}{\tau_T} - \frac{P_0}{\tau_{ex}} \\ -\frac{P_1}{\tau_{10}} - \frac{P_1}{\tau_{isc}} + \frac{P_0}{\tau_{ex}} \\ \frac{P_1}{\tau_{isc}} - \frac{P_T}{\tau_T} \end{bmatrix}$$
(3.1)

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$$\bar{I}_{f}(\vec{r}) = \gamma(\vec{r}) \left(1 - \frac{\tau_{T} P_{T}^{eq} \left(1 - \exp\left(-\frac{(T_{p} - t_{p})}{\tau_{T}} \right) \right)}{1 - \exp\left(-\frac{(T_{p} - t_{p})}{\tau_{T}} + k_{2} t_{p} \right)} \times \frac{\left(\exp\left(k_{2} t_{p} \right) - 1 \right)}{t_{p}} \right)$$
(3.2)

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4 Another chapter

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4.1 One section

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4.1.1 One subsection

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Chapter 4. Another chapter

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A An appendix

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Personal details:

Name : Mr. Sample CV Address : Samplestreet

70

6005 Luzern Switzerland

Date of Birth: 2nd of October 1981

Nationality: Swiss

Legally work : legally work in EU
Marital status : with partner
Children : none

Languages : Chinese/Mandarin, English, French, German

Education level: Bachelors degree

Hospitality work 3-5 years

experience :

Special experience : Europe work experience

Date of availability : September 2009

Current location: Africa

Travelling Status : will be travelling single status

Telephone : 0041 41 370 6759 Email address : jeff@h-g-r.com

Position(s) sought : Permanent position for graduates
Department(s) sought : Food & Beverage Bar/Sommelier

Personal profile:

As a Bachelor of Business Administration and after obtaining first relevant international work experience within the hospitality industry, I am now ready to take on new responsibilities to further my professional career. My key strengths include strong analytical and logical skills, an eye for detail, communication and interpersonal skills.

I enjoy working in a team and help others progress. At the same time I work well independently. As a highly motivated and driven individual I strive on taking up challenges.

Interests:

Travelling Foreign Cultures Photography Sports

Educational qualifications:

Oct 99 - Feb 02 Higher Diploma (Hotel Management)

Swiss Hotelmanagement School, SHL

Employment history:

Mar 04 - Ongoing Assistant Manager (Rooms Division/Food & Beverage)

Hotel Atlantic Kempinski Hamburg www.kempinski.com 5 star business hotel, part of Leading Hotels of the World 412 guest rooms, large function facilities, 3

food & beverage outlets

Optimization of bar procedures, reinforcing SOPs

Developing & implementing promotions Responsible for day-to-day operations

Optimization and streamlining of housekeeping and laundry procedures

Implementation of new SOPs

Analyzing monthly reports for rooms division performance and sub departments

Mar 03 - Mar 04 Management Trainee

Hospitality Graduate Recruitment www.h-g-r.com Leading company for

placements within the Hospitality industry.

Traineeship covering all aspects of an online recruitment agency.

Mar 02 - Mar 03 Management Trainee (Rooms Division)

Hyatt Regency Xian, China www.hyatt.com 5 star business hotel 404 guest rooms,

4 food & beverage outlets

Traineeship covering all rooms division departments on operational as well as

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Training courses attended:

Mar 02 - Ongoing OpenOffice - IT Courses

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References:

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